

REMARKS

Entry of the above preliminary amendment is respectfully requested. This amendment is submitted in conjunction with a Request for Continuing Examination. The addition of claims has resulted in 5 additional claims (including 2 additional independent claims). Therefore, a check for \$160.00 to cover the fees under 37 CFR §§ 1.16(b) and (c) is enclosed.

Respectfully submitted,



Devin R. Jensen
Registration No. 44,805
Attorney for Applicant
TRASKBRITT, P.C.
P.O. Box 2550
Salt Lake City, Utah 84110
Telephone: (801) 532-1922

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VERSION WITH MARKINGS TO SHOW CHANGES MADE

23. (Amended) [A] An operable gate stack, including a non-crystalline metallic silicide film.

24. (Thrice Amended) [A] An operable gate stack, including an amorphous metallic silicide film wherein said metallic silicide film is substantially devoid of silicon clusters.

25. (Thrice Amended) [A] An operable gate stack on a [dielectric layered] silicon substrate having a dielectric layer thereover, comprising:

a polysilicon layer disposed over said dielectric [layered silicon substrate] layer;
a non-crystalline metallic silicide film disposed over said polysilicon layer; and
a dielectric cap on said non-crystalline metallic silicide film.

26. (Twice Amended) A gate stack structure comprising [a] an operable gate stack on a dielectric [layered] layer, over a silicon substrate, wherein [a gate] said dielectric layer [of said gate stack] is substantially devoid of pitting.

27. (Amended) The gate stack structure of claim 26 wherein said [a] operable gate stack includes a non-crystalline metallic silicide film.

28. (Previously Twice Amended) The gate stack structure of claim 26 wherein said operable gate stack includes an amorphous metallic silicide film substantially devoid of silicon clusters.

29. A semiconductor device, comprising at least one gate stack having a non-crystalline metallic silicide film.

30. The semiconductor device of claim 29, wherein said at least one gate stack comprises:

a silicon substrate having a dielectric layer thereover;

a polysilicon layer disposed over said dielectric layer;

a non-crystalline metallic silicide film disposed over said polysilicon layer; and

a dielectric cap on said non-crystalline metallic silicide film.

31. A semiconductor device, comprising at least one gate stack structure on a dielectric layer, over a silicon substrate, wherein said dielectric layer is substantially devoid of pitting.

32. The semiconductor device of claim 31, wherein said at least one gate stack structure includes a non-crystalline metallic silicide film.

33. The semiconductor device of claim 31, wherein said at least one gate stack structure includes an amorphous silicide film substantially devoid of silicon clusters.